

IN THE CLAIMS:

Claims 1, 7, 24 and 34 have been amended as follows:

1. (Twice Amended) A method for fabricating a semiconductor device comprising:

 a resin sealing step of loading a substrate on which semiconductor elements having protruding electrodes are formed to a mold, and supplying a sealing resin to positions of the protruding electrodes so as to form a resin layer which seals the protruding electrodes and the substrate;

 a protruding electrode exposing step of exposing at least ends of the protruding electrodes from the resin layer; and

 a separating step of cutting the substrate together with the resin layer so that the semiconductor elements are separated from each other,

 wherein the resin sealing step disposes a film between the protruding electrodes and the mold, which thus contacts the sealing resin through the film.

7. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim [3] 1, wherein the sealing resin is provided to the film before the resin sealing step is executed.

24. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim [3] 1, wherein:

the film used in the resin sealing step has projections located in positions corresponding to those of the protruding electrodes; and

the resin layer is formed in a state in which the projections are pressed against the protruding electrodes.

34. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim [3] 1, wherein:

the film used in the resin sealing step has projection or recess portions located in positions in which the film is not interfered with the projecting electrodes; and

recess or projection portions formed on the resin layer by the projection or recess portions are used for positioning after the resin sealing step is completed.